

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph that begins on page 11, line 30 with the following replacement paragraph which shows all changes relative to the previous version of the paragraph:

In a further process step, illustrated in Fig. 2g, a first recess 229 and a second recess 231 are etched using etching mask 223, especially in the openings of the etching mask which are defined by areas 225 and 227. While doing so, first recess 229 is etched through the second insulating layer 221 for exposing the conductive material 219 which fills contact via 217. By analogy therewith, the second recess 231 is etched through the second insulating layer 221 as well as through the first insulating layer 215 for exposing the second terminal surface 213 of the second terminal 211. Since the conductive material 219, which fills contact via 217, extends through the first insulating layer 215 up to the second insulating layer 221, and since the second surface 213 is spaced apart from the substrate surface 203 by a smaller distance than an upper surface of the conductive material 219, the step of etching the first and second recesses ~~225-229~~ and ~~227-231~~ includes undercutting, in etching, the conductive material 219 if, for example, the first recess ~~225-229~~ and the second recess ~~227-231~~ are etched in passes of the same duration, since the depth of the second recess ~~227-231~~ is determined by a position of the second surface 213 of the second terminal 211. While doing so, the second surface 213 is less exposed to an etching attack, since etching is performed only up to the second surface

213. On the other hand, the conductive material 219, which fills contact via 217, is a connecting piece with the first terminal 205, so that any initial etching of the conductive material 219 does not have any negative repercussions on an operation of the arrangement, all the more so since the first recess ~~225~~229 does not extend up to the first surface 207 of the first terminal 205.

Please replace the paragraph that begins on page 13, line 23 with the following replacement paragraph which shows all changes relative to the previous version of the paragraph:

The process steps described by means of Fig. 2h clearly show that the same etching mask 223 is used for forming the first recess 229 and the second recess 231 as well as for creating the first contact terminal 237 and the second contact terminal 239. If the conductive material 233 and the conductive material 235 are the same conductive material, the first contact terminal 237 and the second contact terminal 239 may be produced in one pass, whereby a contacting of the second terminal 211, for example with the wiring plane, is effected at the same time. While doing so, a contact with the second terminal surface 213 of the second terminal 211 may be structured with any desired degree of precision, so that, e.g., a sufficiently large contact area with the second terminal 211 may be realized, e.g. to achieve a small transition impedance towards the second terminal 211.

Please replace the paragraph that begins on page 14, line 1 with the following replacement paragraph which shows all changes relative to the previous version of the paragraph:

In addition, due to the undercutting, shown in Fig. 2g and Fig. 2h, in the formation of the first recess 229, the conductive material 219 filling contact via 217 is exposed such that the conductive material 233 contacts the conductive material ~~243~~ 219, which fills contact via 217, both laterally and on the upper surface of the conductive material 219, so that, for example, a transition impedance towards the first terminal 205 is reduced. Due to the fact that the conductive material 219 may be structured in a precise manner on the first surface 207 of the first terminal 205, a small transition impedance is to be expected there as well, whereby, e.g., the electrical properties of the arrangement manufactured in accordance with the invention are improved.